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Kind regards,

Team Nexperia

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

Rev. 5 — 21 December 2011

Product data sheet

1. Product profile

1.1 General description

PNP/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1.	Product	overview
	1 I Oudot	010111011

Type number	Package		NPN/PNP		Package
	NXP	JEITA	complement	complement	configuration
PEMB18	SOT666	-	PEMD18	PEMH18	ultra small and flat lead
PUMB18	SOT363	SC-88	PUMD18	PUMH18	very small

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- 1.3 Applications
 - Low current peripheral driver
 - Control of IC inputs
 - Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
lo	output current		-	-	-100	mA
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		1.7	2.1	2.6	
-						



- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1

| | 2 3 006aaa212

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1	001aab555	

3. Ordering information

Table 4. Ord	Table 4. Ordering information				
Type number	Package				
	Name	Description	Version		
PEMB18	-	plastic surface-mounted package; 6 leads	SOT666		
PUMB18	SC-88	plastic surface-mounted package; 6 leads	SOT363		

4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
PEMB18	6A
PUMB18	B8*

[1] * = placeholder for manufacturing site code

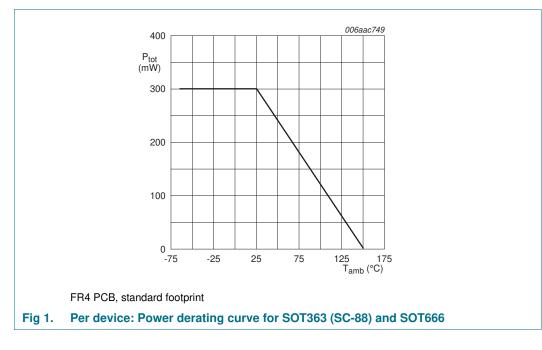
5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V _{CBO}	collector-base voltage	open emitter	-	-50	V
V _{CEO}	collector-emitter voltage	open base	-	-50	V
V _{EBO}	emitter-base voltage	open collector	-	-7	V
VI	input voltage				
	positive		-	+7	V
	negative		-	-20	V
lo	output current		-	-100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	PEMB18 (SOT666)		<u>[1][2]</u> _	200	mW
	PUMB18 (SOT363)		<u>[1]</u> -	200	mW
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	PEMB18 (SOT666)		<u>[1][2]</u> _	300	mW
	PUMB18 (SOT363)		<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω



6. Thermal characteristics

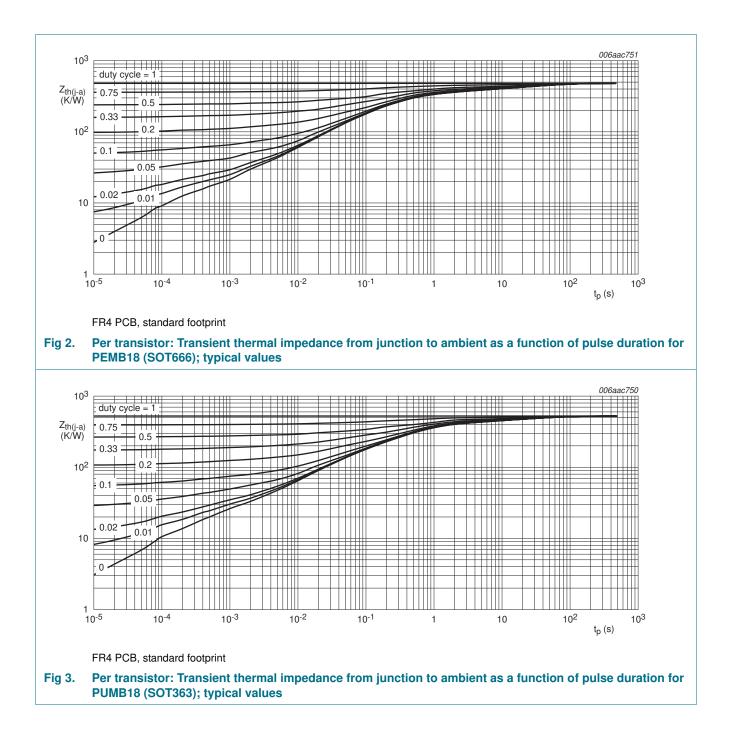
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	istor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	PEMB18 (SOT666)		<u>[1][2]</u> _	-	625	K/W
	PUMB18 (SOT363)		<u>[1]</u> _	-	625	K/W
Per devic	e					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	PEMB18 (SOT666)		[1][2] _	-	417	K/W
	PUMB18 (SOT363)		[1] -	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PEMB18; PUMB18

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω



7. Characteristics

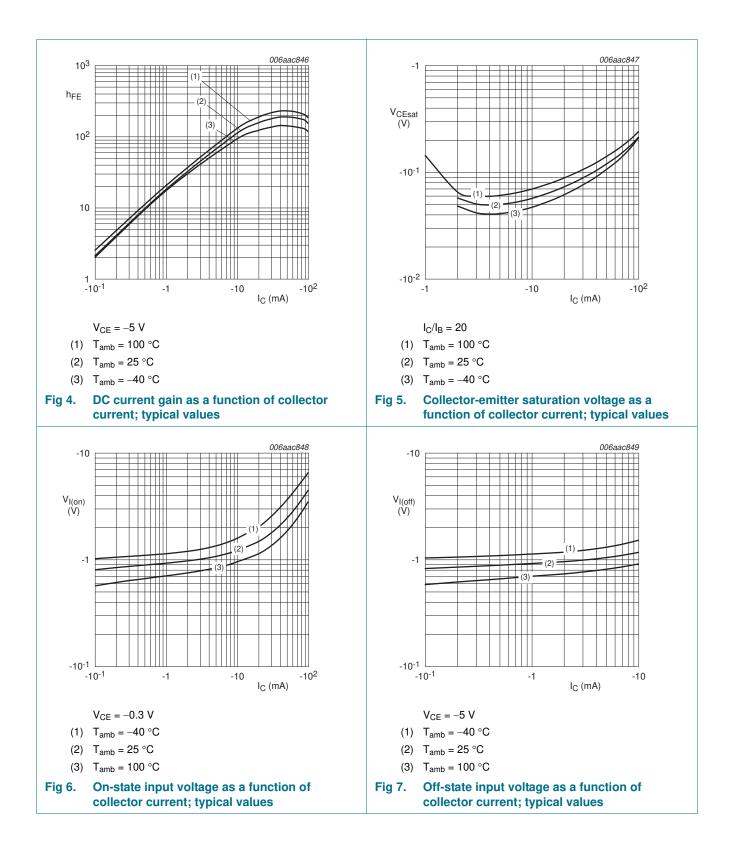
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter cut-off	$V_{CE} = -30 \text{ V}; \text{ I}_{B} = 0 \text{ A}$	-	-	-1	μA
current	$\label{eq:Vce} \begin{array}{l} V_{CE} = -30 \ \text{V}; \ \text{I}_{B} = 0 \ \text{A}; \\ T_{j} = 150 \ ^{\circ}\text{C} \end{array}$	-	-	-5	μA	
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-600	μ A
h _{FE}	DC current gain	$V_{CE} = -5$ V; $I_C = -10$ mA	50	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -10 \text{ mA}; I_{B} = -0.5 \text{ mA}$	-	-	-100	mV
V _{I(off)}	off-state input voltage	V_{CE} = -5 V; I_{C} = $-100~\mu A$	-	-0.9	-0.3	V
V _{I(on)}	on-state input voltage	$V_{CE} = -0.3 \text{ V};$ $I_C = -20 \text{ mA}$	-2.5	-1.5	-	V
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		1.7	2.1	2.6	
C _c	collector capacitance	$\label{eq:VCB} \begin{split} V_{CB} &= -10 \text{ V}; \text{ I}_{E} = i_{e} = 0 \text{ A}; \\ f &= 1 \text{ MHz} \end{split}$	-	-	3	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_C = -10 \text{ mA};$ f = 100 MHz	1 -	180	-	MHz

[1] Characteristics of built-in transistor

PEMB18_PUMB18 Product data sheet

PEMB18; PUMB18

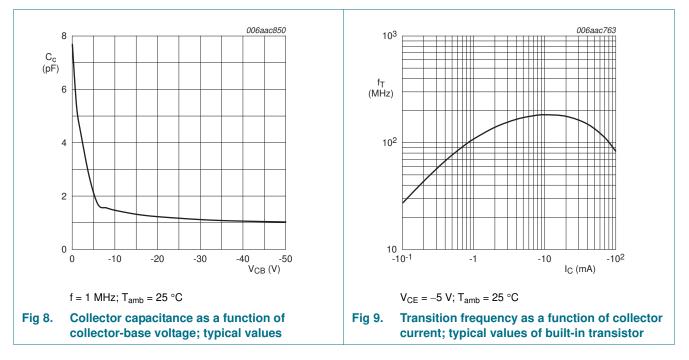
PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω



PEMB18_PUMB18 Product data sheet

PEMB18; PUMB18

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

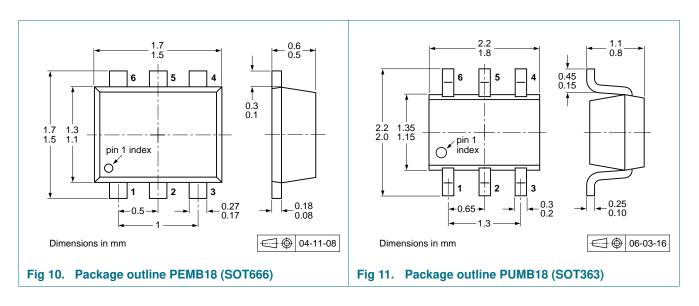


8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

10. Packing information

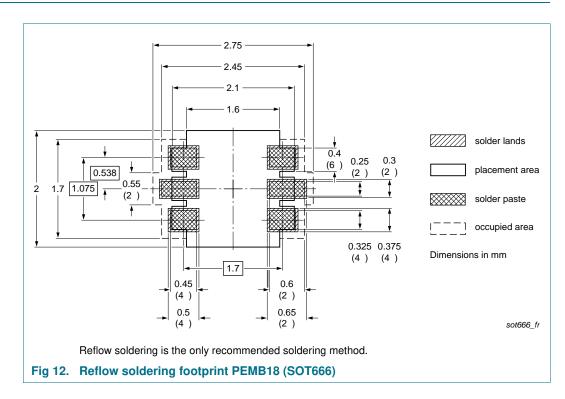
Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

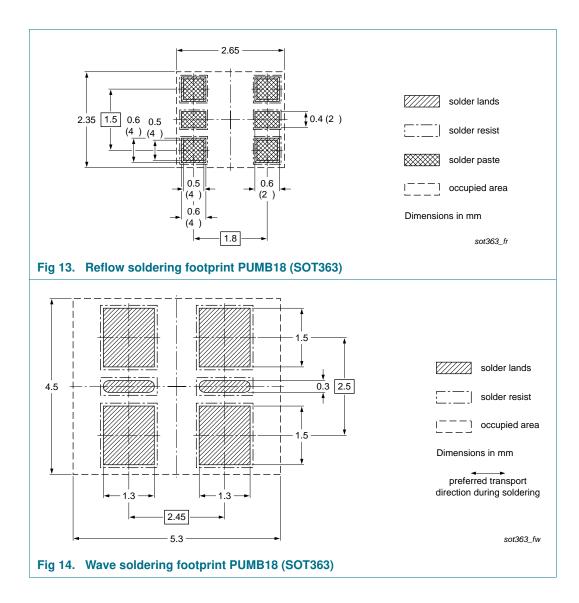
Туре	Package	Package Description			Packing quantity			
number				3000	4000	8000	10000	
PEMB18	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-	
		4 mm pitch, 8 mm tape and reel		-	-115	-	-	
PUMB18 SOT363		4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135	
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165	

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

11. Soldering



PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω



12. Revision history

Table 10.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMB18_PUMB18 v.5	20111221	Product data sheet	-	PEMB18_PUMB18 v.4
Modifications:	 Section 4 "M Figure 1 to 3 Section 6 "TI Figure 4 to 7 Table 8 "Cha Section 8 "Te 	roduct profile": updated arking": updated , <u>8</u> and <u>9</u> : added hermal characteristics": up : updated aracteristics": I _{CEO} and V _{CE} est information": added Soldering": added		
	 Section 13 "I 	<u>_egal information"</u> : updated	b	
PEMB18_PUMB18 v.4	20090901	Product data sheet	-	PEMB18_PUMB18 v.3
PEMB18_PUMB18 v.3	20050708	Product data sheet	-	PEMB18_PUMB18 v.2
PEMB18_PUMB18 v.2	20050202	Product data sheet	-	PUMB18 v.1
PUMB18 v.1	20031003	Product specification	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PEMB18_PUMB18

Product data sheet

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

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PEMB18_PUMB18 Product data sheet

PEMB18; PUMB18

PNP/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 10 k Ω

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